

N-Channel MOSFET

Description

The WSD1614DN106 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a Battery protection or in other Switching application.

Features

High power and current handing capability
Lead free product is acquired
Surface mount package
ESD:1.5KV

Product Summery

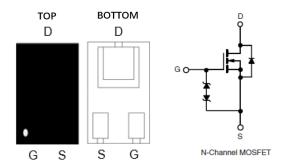
BV _{DSS}	R _{DS(ON)}	I _D	
20V	230mΩ	1.4A	

Application

Battery protection

Load switch

DFN1X06-3S Pin Configuration



Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter	Ratin	Unit	
V _{DS}	Drain-Source Voltage		20	V
V _{GS}	Gate-Source Voltage	±8	V	
,	Drain Current (Continuous) *AC	T _A =25°C	1.4	А
I _D		T _A =70°C	1.1	А
I _{DM}	Drain Current (Pulse) *B	e) *B		А
P _D	Power Dissipation	T _C =25°C		W
T _J /T _{STG}	Operating Temperature/ Storage Temperature		-55~150	${\mathbb C}$

Thermal Resistance Ratings

Symbol	Parameter	Max	Unit	
R_{thJA}	Maximum Junction-to-Ambient	Steady-State	180	°C/W



Electrical Characteristics (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V _G S = 0V, I _D = 250μA	20			V
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 16V, V _{GS} = 0V			1	μA
V _{GS(TH)}	Gate Threshold Voltage	Vgs = Vps, Ips= 250µA	0.4	0.65	1	V
Igss	Gate Leakage Current	Vgs= 8V, Vps=0V			10	μA
		Vgs = 4.5V, ID = 0.55A		180	230	mΩ
RDS(on)	Drain-Source On-state Resistance	Vgs = 2.5V, ID = 0.45A		235	305	mΩ
		Vgs = 1.8V, ID = 0.35A		320	455	mΩ
VsD	Diode Forward Voltage	Isp= 0.35A , Vgs=0V			1.2	V
Is	Diode Forward Current *AC	T _A =25°C			0.58	А
Qg	Total Gate Charge	— Vss=4.5V,		2		nC
Qgs	Gate-Source Charge	V _{DS} =10V, V _{DS} =10V, I _D =1A		0.3		nC
Qgd	Gate-Drain Charge	ID- IA		0.3	1	nC
td (on)	Turn-on Delay Time			1.2		ns
tr	Turn-on Rise Time	V _{GS} =4.5V, V _{DS} =10V,		25		ns
td(off)	Turn-off Delay Time	Rg=6 ,		14		ns
tr	Turn-Off Fall Time			15		ns
Ciss	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz		43	-	pF
Coss	Output Capacitance			9	-	pF
Crss	Reverse Transfer Capacitance	I-1.UIVIΠZ		6		pF

Note:

A: The value of R_{BJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper,

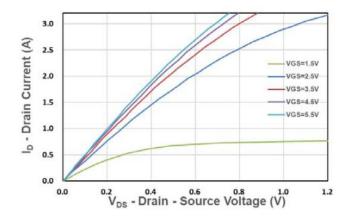
in a still air environment with T_A =25°C. The value in any given application depends

on the user's specific board design.

- B: Repetitive rating, pulse width limited by junction temperature.
- C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



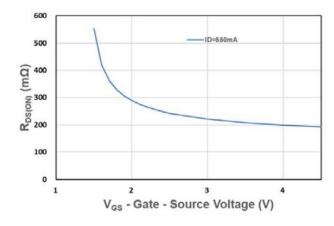
Typical Performance Characteristics ((TJ = 25 °C, unless otherwise noted))



600 500 VGS=1.8V VGS=2.5V VGS=4.5V VGS=4.5V 100 0 0.0 0.5 1.0 1.5 2.0 2.5 3.0 I_D- Drain Current (A)

Figure 1. Output Characteristics

Figure 2. On-Resistance vs. I



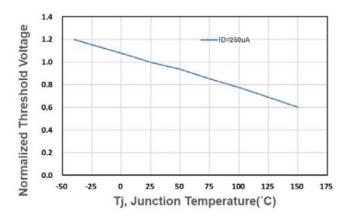
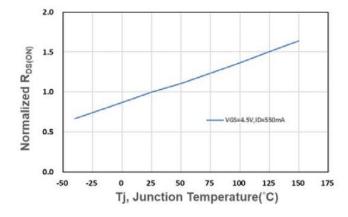


Figure 3. On-Resistance vs. VGS

Figure 4. Gate Threshold Voltage



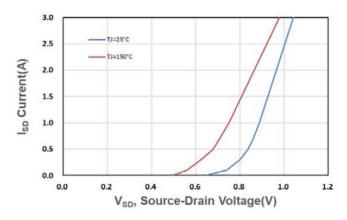


Figure 5. Drain-Source On Resistance

Figure 6. Source-Drain Diode Forward



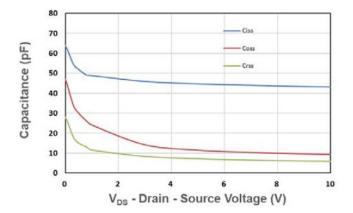


Figure 7. Capacitance

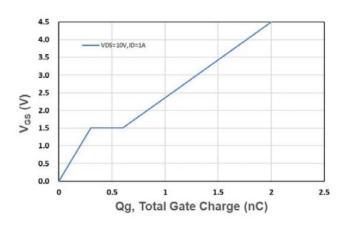


Figure 8. Gate Charge Characteristics

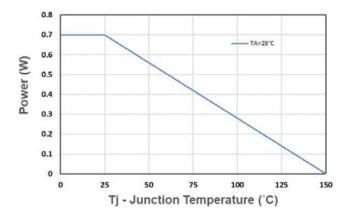


Figure 9. Power Dissipation

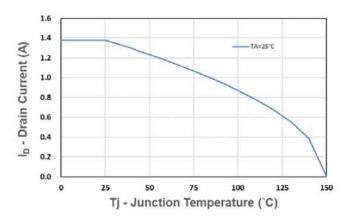


Figure 10. Drain Current

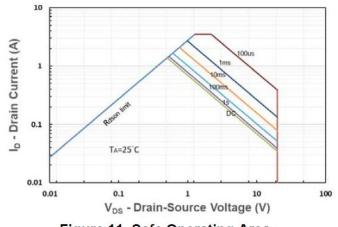


Figure 11. Safe Operating Area

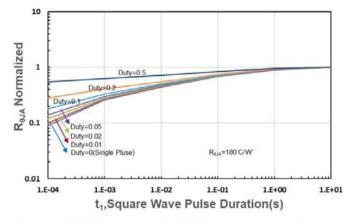
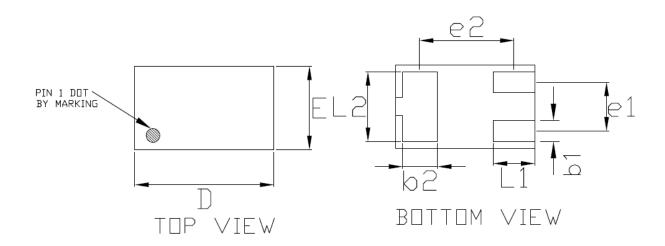


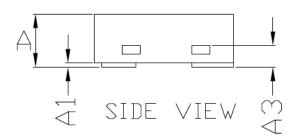
Figure 12. Reja Transient Thermal Impedance

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Package Information

DFN1X06-3S





COMMON DIMENSIONS(MM)					
PKG.	X1:EXTREME THIN				
REF.	MIN.	N□M,	MAX		
Α	>0.40	_	0,50		
A1	0.00	_	0,05		
A3		0.125 REF.			
D	0,95	1.00	1.05		
E	0,55	0.60	0.65		
b1	0,10	0,15	0,20		
b2	0.20	0.25	0.30		
∟1	0,20	0.30	0.40		
L2	0.40	0.50	0,60		
e1	0,35 BSC				
e2	0.675 BSC				



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